

1     ABSTRACT OF THE DISCLOSURE

2             A chemical-mechanical polishing (CMP) method includes applying  
3     a solid abrasive material to a substrate, polishing the substrate,  
4     flocculating at least a portion of the abrasive material, and removing at  
5     least a majority portion of the flocculated portion from the substrate.  
6     Applying solid abrasive material can include applying a CMP slurry or  
7     a polishing pad comprising abrasive material. Such a method can further  
8     include applying a surfactant comprising material to the substrate to  
9     assist in effectuating flocculation of the abrasive material. Such  
10    surfactant comprising material may be cationic which includes, for  
11    example, a quaternary ammonium substituted salt. Also, for example,  
12    the surfactant comprising material may be applied during polishing, brush  
13    scrubbing, pressure spraying, or buffing.

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